

ABSTRACT OF THE DISCLOSURE

In an electron-emitting device including, between electrodes, an electroconductive film having an electron emitting region, the electroconductive film has a film formed in the electron emitting region and made primarily of a material having the higher melting point than that of a material of the electroconductive film. Alternatively, the electroconductive film has a film formed in the electron emitting region and made primarily of a material having a higher temperature, at which the material develops a vapor pressure of 1.3×10^{-3} Pa, than that of a material of the electroconductive film. A manufacture method of an electron-emitting device includes a step of forming a film made primarily of a metal in the electron emitting region of the electroconductive film. The electron-emitting device has stable characteristics and improved efficiency of electron emission. An image-forming apparatus comprising the electron-emitting devices has high luminance and excellent stability in operation.